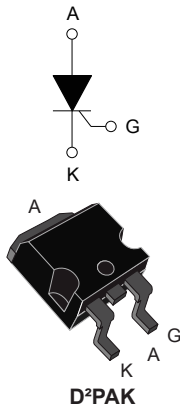



## 30 A – 1200 V automotive grade SCR Thyristor



### Features

- AEC-Q101 qualified 
- High junction temperature:  $T_j = 150\text{ }^{\circ}\text{C}$
- AC off state voltage:  $\pm 1200\text{ V}$
- Nominal on-state current:  $30\text{ A}_{\text{RMS}}$
- High noise immunity:  $1000\text{ V}/\mu\text{s}$
- Max. gate triggering current:  $50\text{ mA}$
- **ECOPACK®2** compliant component

### Applications

- Automotive applications: on board and off board battery charger
- Renewable energy inverters
- Solid state relay
- 3-Phase heating or motor soft start control
- UPS (uninterruptible power supply)
- Bypass SSR / hybrid relay
- Inrush current limiter in battery charger
- AC-DC voltage controlled rectifier
- Industrial welding systems

### Description

The **TN3050H-12GY-TR** is an automotive grade SCR Thyristor designed for applications such as automotive on-board chargers, AC solid state relays and stationary battery chargers.

Rated for a  $30\text{ A}_{\text{RMS}}$  power switching, This SCR Thyristor offers superior performance in terms of peak voltage robustness (up to  $1400\text{ V}$ ) and surge current handling (sine wave pulse up to  $300\text{ A}$ ). Its key features allow the design of functions such as a  $42\text{ A}_{\text{RMS}}$  AC switch (dual back-to-back SCRs) and a  $38\text{ A}$  average AC-DC controlled rectifier bridge for inrush current limitation.

Available in D²PAK package, it is ideal for compact SMD designs on surface mount boards or insulated metal substrate boards.

#### Product status link

[TN3050H-12GY-TR](#)

#### Product summary

$I_{\text{T(RMS)}}$	30 A
$V_{\text{DRM}}/V_{\text{RRM}}$	1200 V
$V_{\text{DSM}}/V_{\text{RSM}}$	1400 V
$I_{\text{GT}}$	50 mA
$T_j$	150 °C

# 1 Characteristics

**Table 1. Absolute ratings (limiting values)**

Symbol	Parameter			Value	Unit
I <sub>T(RMS)</sub>	RMS on-state current (180 ° conduction angle)		T <sub>C</sub> = 126 °C	30	A
I <sub>T(AV)</sub>	Average on-state current (180 ° conduction angle)			19	A
I <sub>TSM</sub> <sup>(1)</sup>	Non repetitive surge peak on-state current, V <sub>R</sub> = 0 V	t <sub>p</sub> = 8.3 ms	T <sub>j</sub> initial = 25 °C	330	A
		t <sub>p</sub> = 10 ms		300	
V <sub>DRM</sub> / V <sub>RRM</sub>	Repetitive off-state voltage (50-60 Hz)		T <sub>j</sub> = 150 °C	1200	V
di/dt	Critical rate of rise of on-state current I <sub>G</sub> = 2 x I <sub>GT</sub> , tr ≤ 100 ns	f = 50 Hz	T <sub>j</sub> = 150 °C	200	A/μs
V <sub>GM</sub>	Peak forward gate voltage	t <sub>p</sub> = 20 μs	T <sub>j</sub> = 150 °C	10	V
I <sub>GM</sub>	Peak forward gate current			8	A
P <sub>G(AV)</sub>	Average gate power dissipation		T <sub>j</sub> = 150 °C	1	W
V <sub>RGM</sub>	Peak reverse gate voltage		T <sub>j</sub> = 25 °C	5	V
T <sub>stg</sub>	Storage junction temperature range			-40 to +150	°C
T <sub>j</sub>	Operating junction temperature			-40 to +150	°C

1. ST recommend  $I^2t$  value for fusing = 450 A<sup>2</sup>s for  $T_j = 25\text{ °C}$  and  $t_p = 10\text{ ms}$

**Table 2. Electrical characteristics ( $T_j = 25\text{ °C}$  unless otherwise specified)**

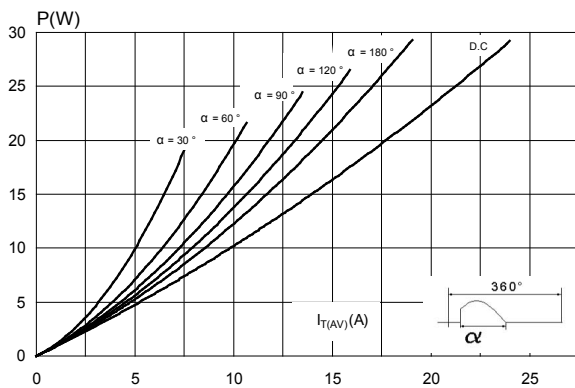
Symbol	Test conditions		Value	Unit	
$I_{GT}$	$V_D = 12\text{ V}$ , $R_L = 33\text{ }\Omega$		Min.	10	mA
			Max.	50	
$V_{GT}$	$V_D = 12\text{ V}$ , $R_L = 33\text{ }\Omega$		Max.	1.3	V
$V_{GD}$	$V_D = 2/3 \times V_{DRM}$ , $R_L = 3.3\text{ k}\Omega$	$T_j = 150\text{ }^\circ\text{C}$	Min.	0.2	V
$I_H$	$I_T = 500\text{ mA}$ , gate open		Max.	100	mA
$I_L$	$I_G = 1.2 \times I_{GT}$		Max.	125	mA
$t_{gt}$	$I_T = 60\text{ A}$ , $V_D = 2/3 \times V_{DRM}$ , $I_G = 100\text{ mA}$ , $dI_G/dt = 0.2\text{ A}/\mu\text{s}$		Typ.	1	$\mu\text{s}$
$dV/dt$	$V_D = 2/3 \times V_{DRM}$ , gate open	$T_j = 150\text{ }^\circ\text{C}$	Min.	1000	$\text{V}/\mu\text{s}$
$t_q$	$I_T = 20\text{ A}$ , $dI_T/dt = 10\text{ A}/\mu\text{s}$ , $V_R = 75\text{ V}$ , $V_D = 2/3 \times V_{DRM}$ , $dV_D/dt = 20\text{ V}/\mu\text{s}$ , $t_p = 100\text{ }\mu\text{s}$	$T_j = 150\text{ }^\circ\text{C}$	Typ.	150	$\mu\text{s}$
$V_{TM}$	$I_{TM} = 60\text{ A}$ , $t_p = 380\text{ }\mu\text{s}$		Max.	1.65	V
$V_{TO}$	Threshold voltage	$T_j = 150\text{ }^\circ\text{C}$	Max.	0.88	V
$R_D$	Dynamic resistance	$T_j = 150\text{ }^\circ\text{C}$	Max.	14	$\text{m}\Omega$
$I_{DRM}/I_{RRM}$	$V_D = V_{DRM}$ , $V_R = V_{RRM}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	5	$\mu\text{A}$
		$T_j = 125\text{ }^\circ\text{C}$	Max.	3	mA
		$T_j = 150\text{ }^\circ\text{C}$	Max.	5	mA
$I_{DSM}/I_{RSM}$	$V_D = V_{DSM}$ , $V_R = V_{RSM}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	10	$\mu\text{A}$

**Table 3. Thermal parameters**

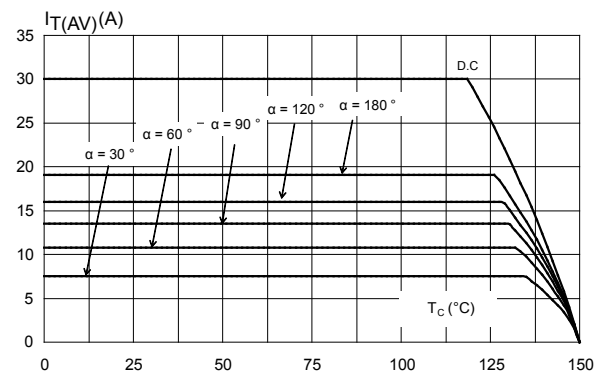
Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (DC, max.)	D <sup>2</sup> PAK	0.8	°C/W
$R_{th(j-a)}$	Junction to ambient (DC, typ., $S_{cu} = 1 \text{ cm}^2$ )		45	

## 1.1 Characteristics (curves)

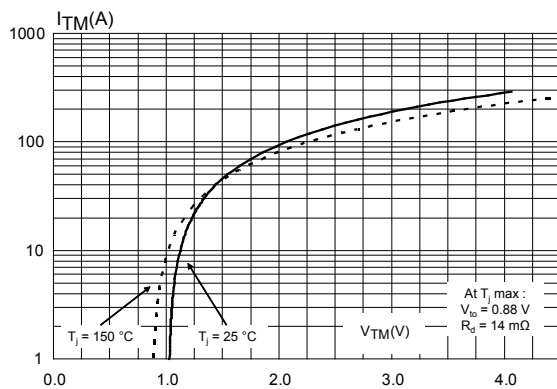
**Figure 1. Maximum average power dissipation versus average on-state current**



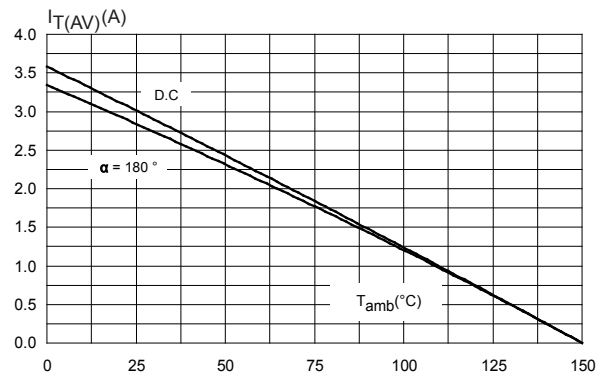
**Figure 2. Average and DC on-state current versus case temperature**



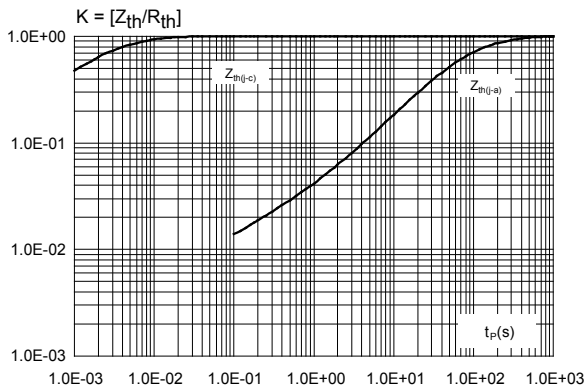
**Figure 3. On-state characteristics (maximum values)**



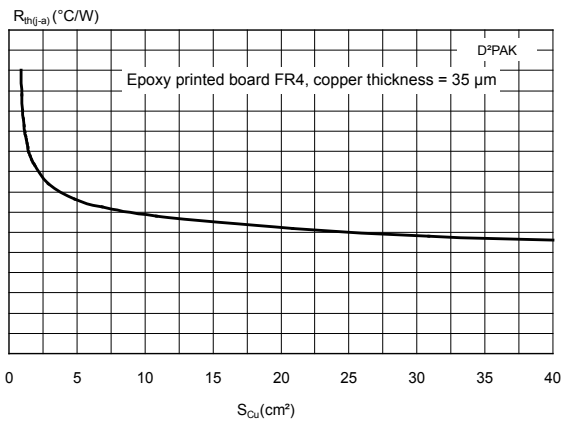
**Figure 4. Average and D.C. on-state current versus ambient temperature**



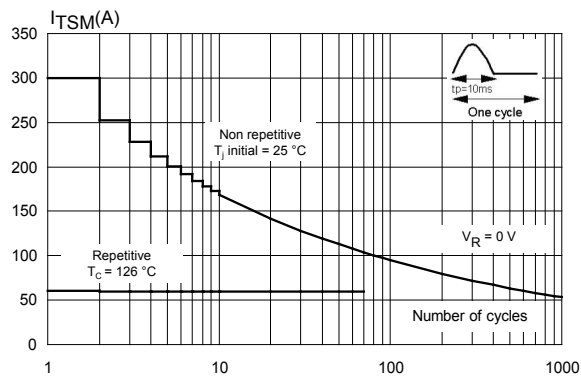
**Figure 5. Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration**



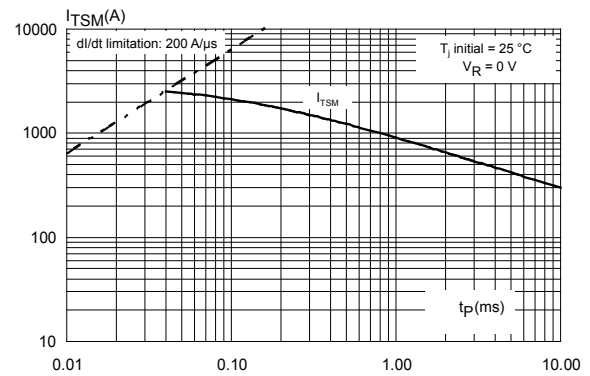
**Figure 6. Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35  $\mu\text{m}$ )**



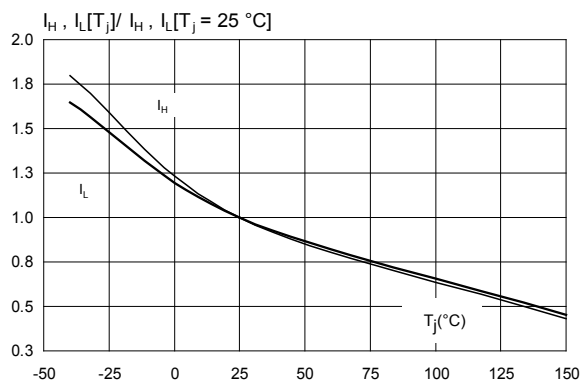
**Figure 7. Surge peak on-state current versus number of cycles**



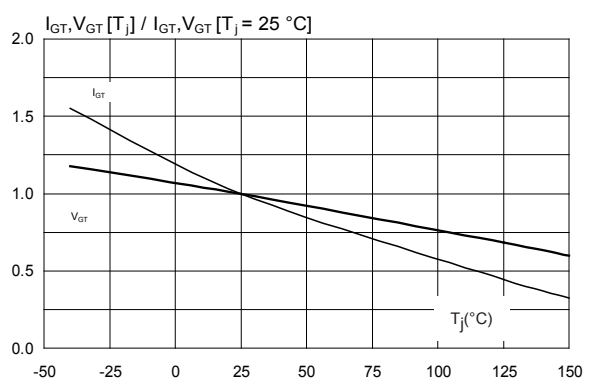
**Figure 8. Non repetitive surge peak on-state current for a sinusoidal pulse ( $t_p < 10 \text{ ms}$ )**



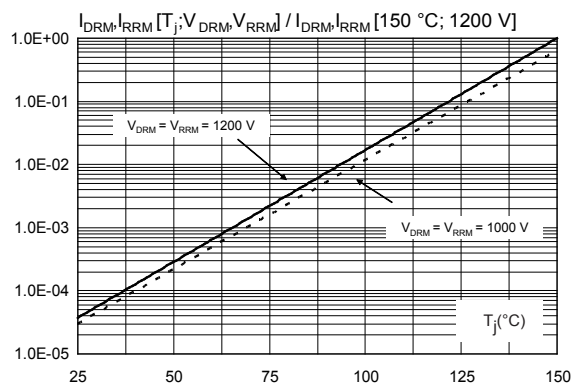
**Figure 9. Relative variation of holding and latching current versus junction temperature (typical values)**



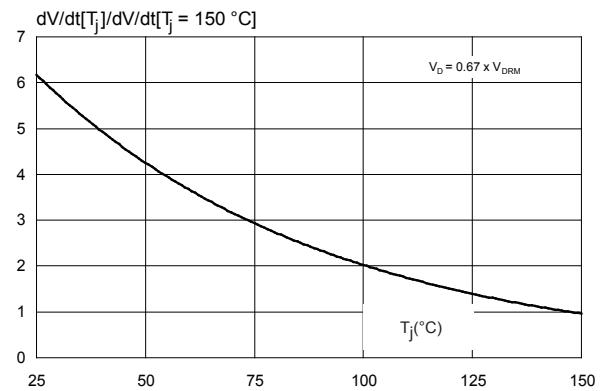
**Figure 10. Relative variation of gate triggering current and voltage versus junction temperature**



**Figure 11. Relative variation of leakage current versus junction temperature for different values of blocking voltage**



**Figure 12. Relative variation of the static dV/dt immunity versus junction temperature (typical values)**



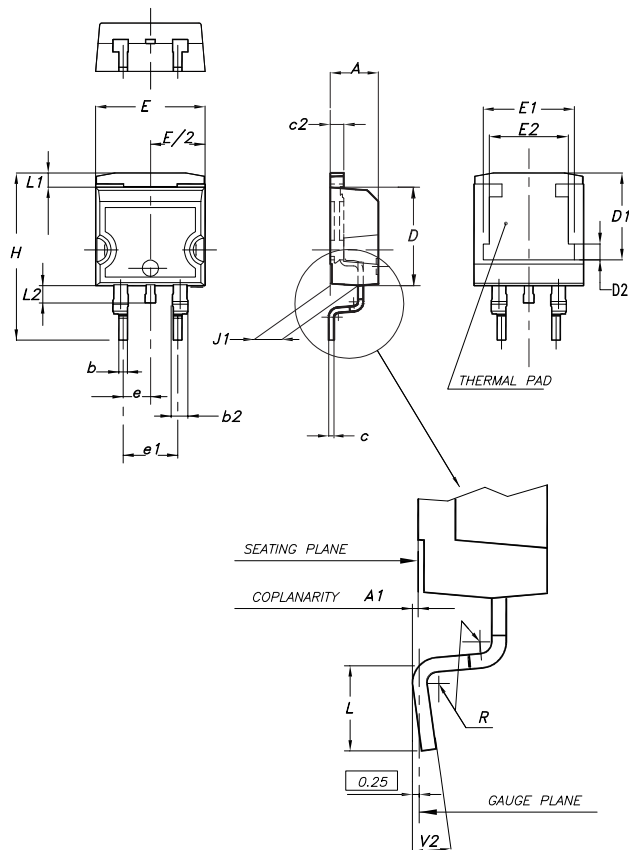
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 D<sup>2</sup>PAK package information

- Package molding resin is halogen free and meets UL94 level V0
- Lead-free package leads
- Cooling method: by conduction (C)

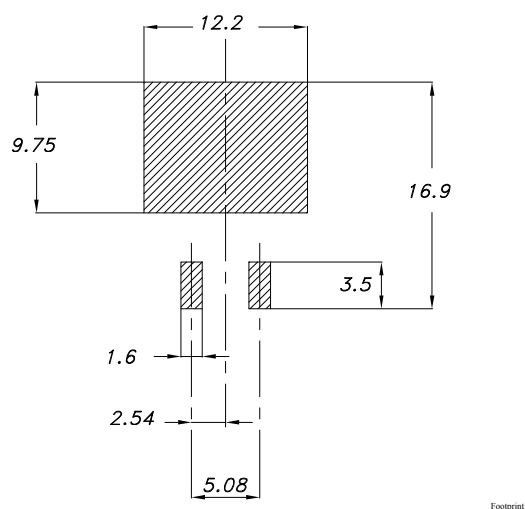
**Figure 13. D<sup>2</sup>PAK package outline**



**Table 4. D<sup>2</sup>PAK package mechanical data**

Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.1732		0.1811
A1	0.03		0.23	0.0012		0.0091
b	0.70		0.93	0.0276		0.0366
b2	1.14		1.70	0.0449		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.23		1.36	0.0484		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50	7.75	8.00	0.2953	0.3051	0.3150
D2	1.10	1.30	1.50	0.0433	0.0511	0.0591
E	10		10.40	0.3937		0.4094
E1	8.50	8.70	8.90	0.3346	0.3425	0.3504
E2	6.85	7.05	7.25	0.2697	0.2776	0.2854
e		2.54			0.1000	
e1	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
J1	2.49		2.69	0.0980		0.1059
L	2.29		2.79	0.0902		0.1098
L1	1.27		1.40	0.0500		0.0551
L2	1.30		1.75	0.0512		0.0689
R		0.4			0.0157	
V2	0°		8°	0°		8°

1. Dimensions in inches are given for reference only

**Figure 14. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)**


### 3 Ordering information

**Table 5. Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN3050H-12GY-TR	TN3050H12Y	D <sup>2</sup> PAK	1.4 g	1000	Tape and reel

## Revision history

**Table 6. Document revision history**

Date	Revision	Changes
01-Sep-2016	1	Initial release.
24-Aug-2017	2	Minor text changes to improve readability. Updated Section "Features", Table 2: "Absolute ratings (limiting values)" and Section 2: "Package information".
17-Sep-2019	3	Updated <a href="#">Section Description</a> and <a href="#">Table 1. Absolute ratings (limiting values)</a> .

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